



## **IRFP360PBF Information**



For Reference Only

**Part Number** IRFP360PBF **Manufacturer** Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 400V 23A TO-247AC

Package TO-247-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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## **Certified Quality**

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









# **IRFP360PBF Specifications**

Manufacturer Part Number         IRFP360PBF           Manufacturer         Vishay Siliconix           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-247-3           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         400V           Current - Continuous Drain (Id) @ 25°C         23A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         210nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         4500pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         280W (Tc)           Rds On (Max) @ Id, Vgs         200 mOhm @ 14A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-247-3           Package / Case         TO-247-3           Report errors?		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-247-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 23A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 10nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max)  FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 280W (Tc) Rds On (Max) @ Id, Vgs Directory Rds On (Max) @ Id, Vgs Through Hole Supplier Device Package TO-247-3 Package / Case  TO-247-3 Package / Case	Manufacturer Part Number	IRFP360PBF
Package         TO-247-3           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         400V           Current - Continuous Drain (Id) @ 25°C         23A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         210nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         4500pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         280W (Tc)           Rds On (Max) @ Id, Vgs         200 mOhm @ 14A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-247-3           Package / Case         TO-247-3	Manufacturer	Vishay Siliconix
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)400VCurrent - Continuous Drain (Id) @ 25°C23A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs210nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4500pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)280W (Tc)Rds On (Max) @ Id, Vgs200 mOhm @ 14A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247-3Package / CaseTO-247-3	Package	TO-247-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)400VCurrent - Continuous Drain (Id) @ 25°C23A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs210nC @ 10VInput Capacitance (Ciss) (Max) @ Vds4500pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)280W (Tc)Rds On (Max) @ Id, Vgs200 mOhm @ 14A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247-3Package / CaseTO-247-3	Series	-
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Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  4500pF @ 25V  Vgs (Max)  ±20V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  200 mOhm @ 14A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-247-3  Package / Case  TO-247-3	Drive Voltage (Max Rds On, Min Rds On)	10V
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Supplier Device Package TO-247-3 Package / Case TO-247-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-247-3	Mounting Type	Through Hole
	Supplier Device Package	TO-247-3
Report errors?	Package / Case	TO-247-3
		Report errors?

### **IRFP360PBF** Guarantees



### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

## **IRFP360PBF Payment Methods**



















## **IRFP360PBF Shipping Methods**













If you have any question about IRFP360PBF, please do not hesitate to contact us!

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